

AP3025PD2BT
3.0 x 2.5 mm Photodiode

DESCRIPTION

- Made with PIN silicon photodiode chips

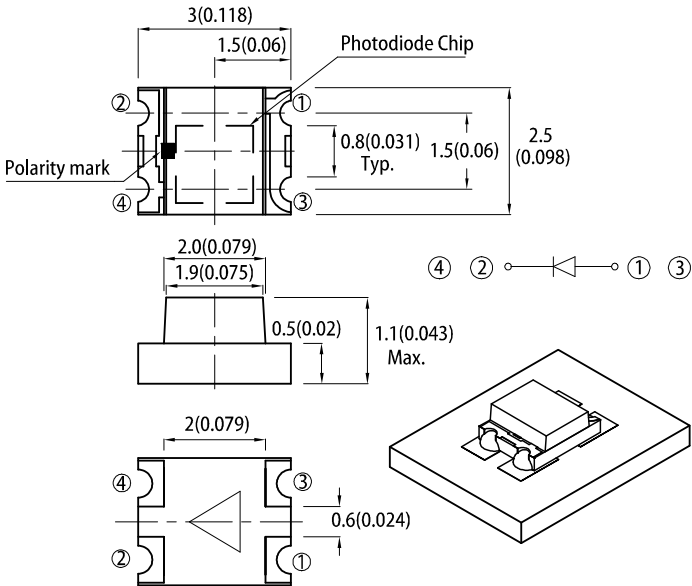
FEATURES

- Package matched with IR emitter APTD1608F3C, APTD1608SF6C, APD3224F3C, APD3224SF4C, APD3224SF6C, APD3224SF7C, and AM2520SF6C09
- Black diffused lens
- Daylight filter
- Package: 2000 pcs / reel
- Moisture sensitivity level: 3
- Halogen-free
- RoHS compliant

APPLICATIONS

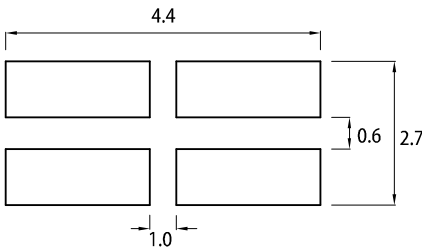
- Infrared applied systems
- Optoelectronic switches
- Photodetector control circuits
- Sensor technology

PACKAGE DIMENSIONS



RECOMMENDED SOLDERING PATTERN

(units : mm; tolerance : ± 0.1)



- Notes:
- All dimensions are in millimeters (inches).
 - Tolerance is $\pm 0.2(0.008)$ unless otherwise noted.
 - The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.
 - The device has a single mounting surface. The device must be mounted according to the specifications.

ABSOLUTE MAXIMUM RATINGS at $T_A=25^{\circ}\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Storage Temperature Range	$-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$	
Operating Temperature Range	$-40^{\circ}\text{C} \sim +85^{\circ}\text{C}$	

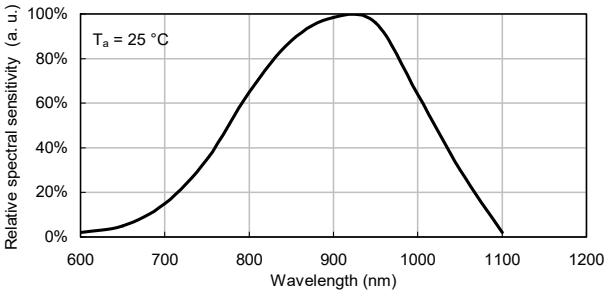
Note:
1. Relative humidity levels maintained between 40% and 60% in production area are recommended to avoid the build-up of static electricity – Ref JEDEC/JESD625-A and JEDEC/J-STD-033.

ELECTRICAL / OPTICAL CHARACTERISTICS at T_A=25°C

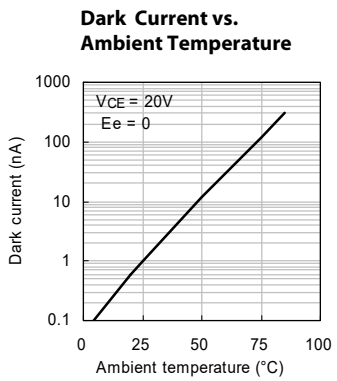
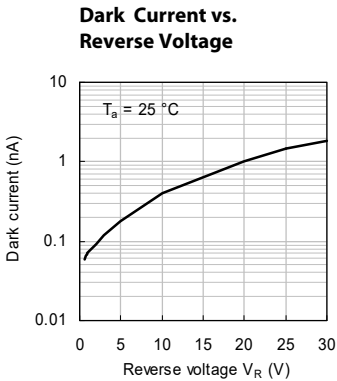
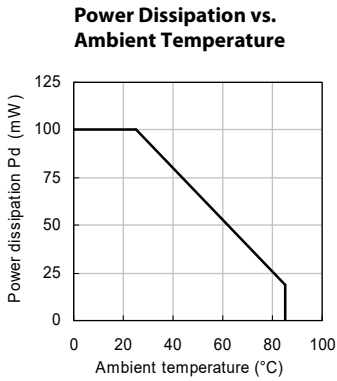
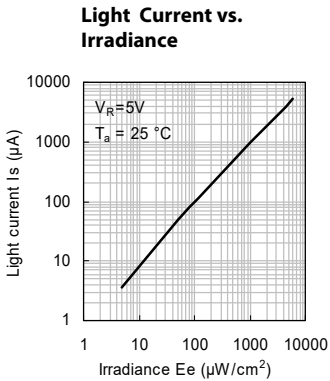
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Break Down Voltage	V _{(BR)R}	33	170	-	V	I _R = 100μA H = 0mW/cm ²
Reverse Dark Current	ID _(R)	-	-	30	nA	V _R = 10V H = 0mW/cm ²
Open Circuit Voltage	V _{OC}	-	390	-	mV	λ = 940nm H = 5mW/cm ²
Rise Time	t _r	-	45	-	ns	V _R = 10V λ = 940nm R _L = 1000Ω
Fall Time	t _f	-	45	-	ns	
Light Current	I _S	40	80	-	μA	V _R = 5V E _e = 0.08mW/cm ² λ = 940nm
Total Capacitance	C _T	-	18	-	pF	V _R = 10V F = 1MHZ H = 0mW/cm ²
Range of Spectral Bandwidth	λ _{0.1}	670	-	1070	nm	-
Wavelength of Peak Sensitivity	λ _p	-	940	-	nm	-

TECHNICAL DATA

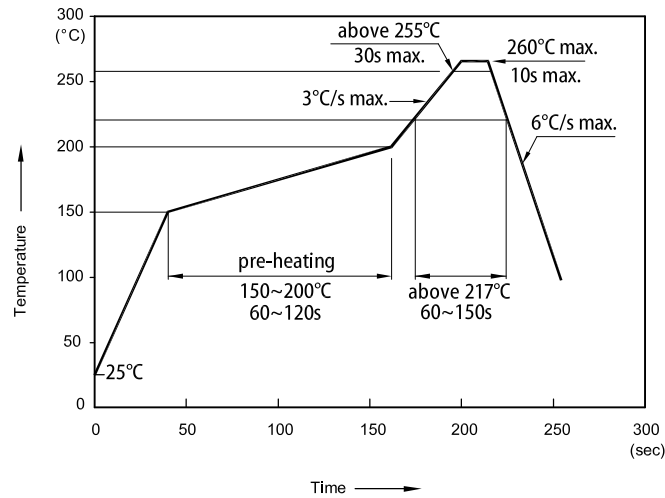
RELATIVE SPECTRAL SENSITIVITY vs. WAVELENGTH



PHOTODIODE

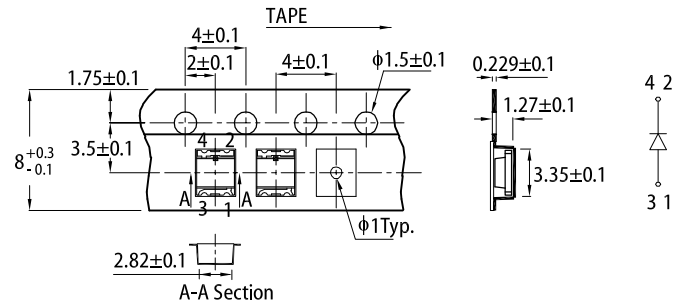


REFLOW SOLDERING PROFILE for LEAD-FREE SMD PROCESS

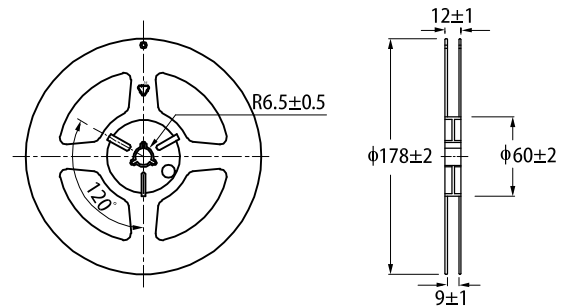


- Notes:
1. Don't cause stress to the LEDs while it is exposed to high temperature.
 2. The maximum number of reflow soldering passes is 2 times.
 3. Reflow soldering is recommended. Other soldering methods are not recommended as they might cause damage to the product.

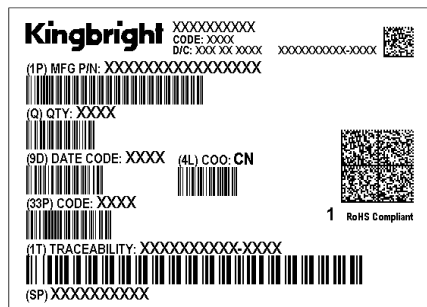
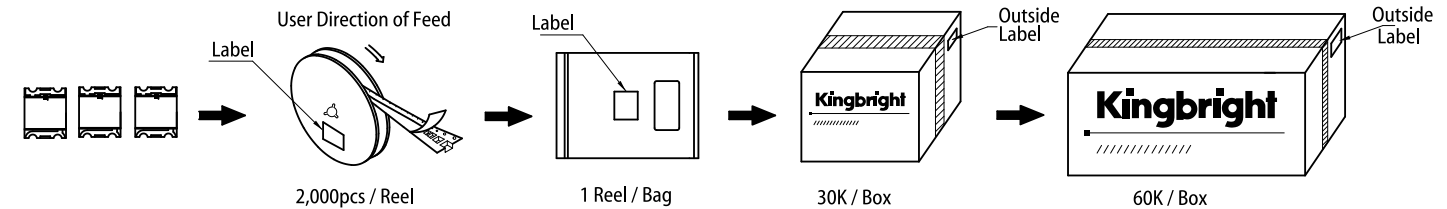
TAPE SPECIFICATIONS (units : mm)



REEL DIMENSION (units : mm)



PACKING & LABEL SPECIFICATIONS



PRECAUTIONARY NOTES

1. The information included in this document reflects representative usage scenarios and is intended for technical reference only.
2. The part number, type, and specifications mentioned in this document are subject to future change and improvement without notice. Before production usage customer should refer to the latest datasheet for the updated specifications.
3. When using the products referenced in this document, please make sure the product is being operated within the environmental and electrical limits specified in the datasheet. If customer usage exceeds the specified limits, Kingbright will not be responsible for any subsequent issues.
4. The information in this document applies to typical usage in consumer electronics applications. If customer's application has special reliability requirements or have life-threatening liabilities, such as automotive or medical usage, please consult with Kingbright representative for further assistance.
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